

**CLEANING OF METALLIC CONTAMINANTS FROM
THE SURFACE OF POLYCRYSTALLINE SILICON**

ABSTRACT

5 A process for removing metallic contaminants
from the surface of chunk or granular polycrystalline
silicon is disclosed. The metallic contaminants are
exposed to a gas-phase halogen etchant which reacts with
the metallic contaminants to form metal halides. The
gas-phase halogen etchant is preferably a halogen plasma.
10 The metal halides are volatilized into an atmosphere
adjacent to the surface of the polycrystalline silicon,
and purged therefrom. The cleaned polycrystalline
silicon is used to prepare a mass of molten silicon for
use in producing a single crystal silicon ingot by the
15 Czochralski method.

